



T-46-07-12

74FCT841A•74FCT841B

10-Bit Transparent Latch with TRI-STATE® Outputs

General Description

The bus interface latch is designed to eliminate the extra packages required to buffer existing latches and provide extra data width for wider address/data paths or buses carrying parity. The 'FCT841A/B is a 10-bit transparent latch, a 10-bit version of the 'FCT373A.

FACT™ FCTA/B utilizes NSC quiet series technology to provide improved quiet output switching and dynamic threshold performance.

FACT FCTA features GTO™ output control and undershoot corrector in addition to a split ground bus for superior performance.

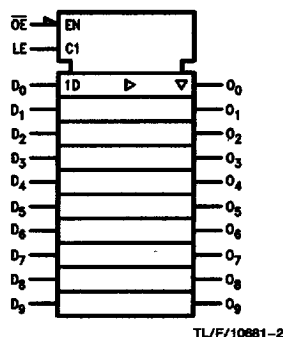
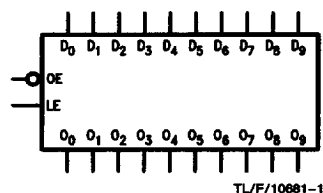
FACT FCTB features an undershoot corrector in addition to a split ground bus for superior performance.

Features

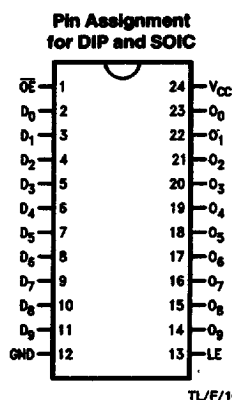
- NSC 74FCT841A/B is pin and functionally equivalent to IDT 74FCT841A/B
- High Speed parallel latches
- Buffered common latch enable
- Input clamp diodes to limit bus reflections
- TTL/CMOS input and output level compatible
- $I_{OL} = 48 \text{ mA (com)}$
- CMOS power levels
- 4 kV minimum ESD immunity

Ordering Code: See Section 8

Logic Symbols



Connection Diagram



Pin Names	Description
D ₀ -D ₉	Data Inputs
O ₀ -O ₉	TRI-STATE Outputs
OE	Output Enable
LE	Latch Enable

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Functional Description

The 'FCT841A/B consists of ten D-type latches with TRI-STATE outputs. The flip-flops appear transparent to the data when Latch Enable (LE) is HIGH. This allows asynchronous operation, as the output transition follows the data in transition.

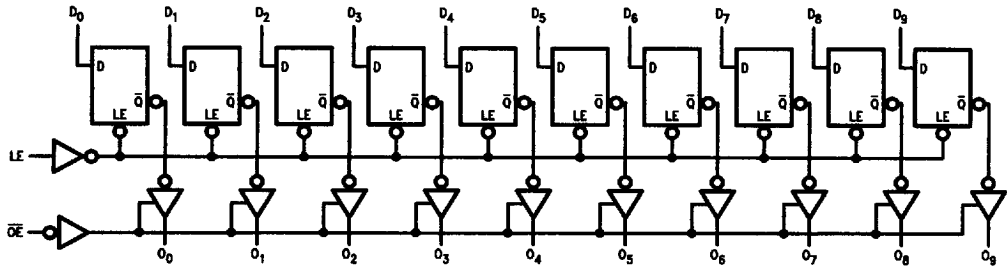
On the LE HIGH-to-LOW transition, the data that meets the setup and hold time is latched. Data appears on the bus when the Output Enable (OE) is LOW. When OE is HIGH the bus output is in the high impedance state.

Function Table

Inputs			Internal	Output	Function
OE	LE	D	Q	O	
A	X	X	X	Z	High Z
H	H	L	L	Z	High Z
H	H	H	H	Z	High Z
H	L	X	NC	Z	Latched
L	H	L	L	L	Transparent
L	H	H	H	H	Transparent
L	L	X	NC	NC	Latched

H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial
Z = High Impedance
NC = No Change

Logic Diagram



TL/F/10681-5

Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Terminal Voltage with Respect to GND (V_{TERM})
74FCTA/B -0.5V to +7.0V

Temperature under Bias (T_{BIAS})
74FCTA/B -55°C to +125°C

Storage Temperature (T_{STG})
74FCTA/B -55°C to +125°C

DC Output Current (I_{OUT}) 120 mA

Note 1: Absolute maximum ratings are those values beyond which damage to the device may occur. Exposure to absolute maximum ratings conditions for extended periods may affect reliability. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables.

Recommended Operating Conditions

Supply Voltage (V_{CC})
74FCTA/B 4.75V to 5.25V

Input Voltage 0V to V_{CC}

Output Voltage 0V to V_{CC}

Operating Temperature (T_A)
74FCTA/B -0°C to +70°C

Junction Temperature (T_J)
PDIP 140°C

Note: All commercial packaging is not recommended for applications requiring greater than 2000 temperature cycles from -40°C to +125°C.

DC Characteristics for 'FCTA/B Family Devices

Typical values are at $V_{CC} = 5.0V$, 25°C ambient and maximum loading. For test conditions shown as Max, use the value specified for the appropriate device type: Com: $V_{CC} = 5.0V \pm 5\%$, $T_A = 0^\circ C$ to $+70^\circ C$; $V_{HC} = V_{CC} - 0.2V$

Symbol	Parameter	74FCTA/B			Units	Conditions	
		Min	Typ	Max			
V_{IH}	Minimum High Level Input Voltage	2.0			V		
V_{IL}	Maximum Low Level Input Voltage			0.8	V		
I_{IH}	Input High Current			5.0 5.0	μA	$V_{CC} = \text{Max}$	$V_I = V_{CC}$ $V_I = 2.7V$ (Note 2)
I_{IL}	Input Low Current			-5.0 -5.0	μA	$V_{CC} = \text{Max}$	$V_I = 0.5V$ (Note 2) $V_I = GND$
I_{OZ}	Maximum TRI-STATE Current			10.0 10.0 -10.0 -10.0	μA	$V_{CC} = \text{Max}$	$V_O = V_{CC}$ $V_O = 2.7V$ (Note 2) $V_O = 0.5V$ (Note 2) $V_O = GND$
V_{IK}	Clamp Diode Voltage	-0.7	-1.2		V	$V_{CC} = \text{Min}; I_{IN} = -18 \text{ mA}$	
I_{OS}	Short Circuit Current	-75	-120		mA	$V_{CC} = \text{Max}$ (Note 1) $V_O = GND$	
V_{OH}	Minimum High Level Output Voltage	2.8 V_{HC} 2.4 2.4	3.0 V_{CC} 4.3 4.3		V	$V_{CC} = 3V; V_{IN} = 0.2V$ or $V_{HC};$ $I_{OH} = -32 \mu A$ $V_{CC} = \text{Min}$ $V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -300 \mu A$ $I_{OL} = -24 \text{ mA}$ (Com)
V_{OL}	Maximum Low Level Output Voltage	GND GND 0.3 0.3	0.2 0.2 0.5 0.5		V	$V_{CC} = 3V; V_{IN} = 0.2V$ or $V_{HC};$ $I_{OH} = 300 \mu A$ $V_{CC} = \text{Min}$ $V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = 300 \mu A$ $I_{OL} = 48 \text{ mA}$ (Com)
I_{CC}	Maximum Quiescent Supply Current		0.2	1.5	mA	$V_{CC} = \text{Max}$ $V_{IN} \geq V_{HC}; V_{IN} \leq 0.2V$ $f_I = 0$	
ΔI_{CC}	Quiescent Supply Current; TTL Inputs HIGH		0.5	2.0	mA	$V_{CC} = \text{Max}$ $V_{IN} = 3.4V$ (Note 3)	
I_{CCD}	Dynamic Power Supply Current (Note 4)		0.50		mA/MHz	$V_{CC} = \text{Max}$ Outputs Open $\overline{OE} = GND$ $LE = V_{CC}$ One Input Toggling 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq 0.2V$

DC Characteristics for 'FCTA/B Family Devices

Typical values are at $V_{CC} = 5.0V$, $25^{\circ}C$ ambient and maximum loading. For test conditions shown as Max, use the value specified for the appropriate device type: Com: $V_{CC} = 5.0V \pm 5\%$, $T_A = 0^{\circ}C$ to $+70^{\circ}C$; $V_{CH} = V_{CC} - 0.2V$ (Continued)

Symbol	Parameter	74FCTA/B			Units	Conditions	
		Min	Typ	Max			
I_C	Total Power Supply Current (Note 6)			5.5	mA	$V_{CC} = \text{Max}$ Outputs Open $\overline{OE} = \text{GND}$ $LE = V_{CC}$ $f_I = 10 \text{ MHz}$ One Bit Toggling 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq 0.2V$
				6.0			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$
				9.0		(Note 5) $V_{CC} = \text{Max}$ Outputs Open $\overline{OE} = \text{GND}$ $LE = V_{CC}$ $f_I = 2.5 \text{ MHz}$ Eight Bits Toggling 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq 0.2V$
				14.5			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$

Note 1: Maximum test duration not to exceed one second, not more than one output shorted at one time.

Note 2: This parameter is guaranteed but not tested.

Note 3: Per TTL driven input ($V_{IN} = 3.4V$); all other inputs at V_{CC} or GND.

Note 4: This parameter is not directly testable, but is derived for use in Total Power Supply calculations.

Note 5: Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.

Note 6: $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$

$$I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_{CP}/2 + f_I N_I)$$

I_{CC} = Quiescent Current

ΔI_{CC} = Power Supply Current for a TTL High Input ($V_{IN} = 3.4V$)

D_H = Duty Cycle for TTL Inputs High

N_T = Number of Inputs at D_H

I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)

f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)

f_I = Input Frequency

N_I = Number of Inputs at f_I

All currents are in milliamps and all frequencies are in megahertz.

AC Electrical Characteristics: See Section 2 for Waveforms

Symbol	Parameter	Test Conditions	74FCTA		74FCTB		Units	Fig. No.
			T _A , V _{CC} = Com		T _A , V _{CC} = Com			
			Min	Max	Min	Max		
t _{PLH} t _{PHL}	Propagation Delay Dn to Qn (LE = High)	C _L = 50 pF R _L = 500Ω	9.0		6.5		ns	2-9
t _{PLH} t _{PHL}	Propagation Delay Dn to Qn (LE = High)	C _L = 300 pF (Note 1) R _L = 500Ω	13.0		13.0		ns	2-9
t _{SU}	Data to LE Setup Time	C _L = 50 pF R _L = 500Ω	2.5		2.5		ns	2-10
t _H	Data to LE Hold Time	C _L = 50 pF R _L = 500Ω	2.5		2.5		ns	2-10
t _{PHL} t _{PLH}	Propagation Delay LE to On	C _L = 50 pF R _L = 500Ω	12.0		8.0		ns	2-9
		C _L = 300 pF (Note 1) R _L = 500Ω	16.0		15.5		ns	2-9
t _W	LE Pulse Width High	C _L = 50 pF R _L = 500Ω	4.0		4.0		ns	2-9

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AC Electrical Characteristics: See Section 2 for Waveforms (Continued)

Symbol	Parameter	Test Conditions	74FCTA		74FCTB		Units	Fig. No.
			T _A , V _{CC} = Com		T _A , V _{CC} = Com			
			Min	Max	Min	Max		
t _{PZH} t _{PZL}	Output Enable Time (OE to On)	C _L = 50 pF R _L = 500Ω		11.5		8.0	ns	2-11
		C _L = 300 pF (Note 1) R _L = 500Ω		23.0		14.0	ns	2-11
t _{PHZ} t _{PLZ}	Output Disable Time (OE to On)	C _L = 5 pF (Note 1) R _L = 500Ω		7.0		6.0	ns	2-11
		C _L = 50 pF R _L = 500Ω		8.0		7.0	ns	2-11

Note 1: These parameters are guaranteed but not tested.

Capacitance T_A = +25°C, f = 1.0 MHz

Symbol	Parameter (Note 1)	Conditions	Typ	Max	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	6	10	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	8	12	pF

Note 1: This parameter is measured at characterization but not tested.